

In the Claims:

Claim 1 (currently amended). In an ~~integrated semiconductor structure~~ a stacked via having a first layer, a second layer, and an intermediate layer, a contact structure extending through the first layer, the second layer, and the intermediate layer for electrically connecting regions of the semiconductor structure, the contact structure comprising:

a first contact hole filling in the first layer; and

a second contact hole filling in the second layer; and

an intermediate structure in the intermediate layer disposed between the first layer and the second layer and connecting said first contact hole filling with said second contact hole filling, said intermediate structure forming an interconnect having a length between longitudinal ends thereof ~~and a given width, and a contact area at each of said longitudinal ends with a contact area width contact area width greater than said given width,~~ said interconnect having a contact area at each of said longitudinal ends with a contact area width perpendicular to said length, and a connecting structure connecting said contact areas, said connecting structure having a connecting structure area with a connecting structure

area width perpendicular to said length, said contact area width being greater than said connecting structure area width.

Claim 2 (previously amended). The contact structure according to claim 1, wherein said interconnect is configured to connect two nearest points of a periodic basic grid disposed on said interconnect, to one another.

Claim 3 (original). The contact structure according to claim 2, wherein said contact area of said intermediate structure is a square contact area at each end of the interconnect.

Claim 4 (original). The contact structure according to claim 3, wherein the contact areas and the interconnect define a bone-shape form of said intermediate structure.

Claim 5 (original). The contact structure according to claim 1, wherein said intermediate layer is a metallization plane, and said intermediate structure is formed of a conductive material of the metallization plane.

Claim 6 (original). The contact structure according to claim 1, wherein said contact hole fillings contain tungsten.

Claim 7 (original). The contact structure according to claim 1, wherein the first and second layers are oxide layers.

Claims 8-9 (canceled).


Claim 10 (previously added). The contact structure according to claim 1, wherein said first contact hole filling and said second contact hole filling are the only contact hole fillings contacting said intermediate structure.

Claim 11 (currently amended). In a DRAM having a first layer, a second layer, and an intermediate layer, a contact structure extending through the first layer, the second layer, and the intermediate layer for electrically connecting regions of the DRAM, the contact structure comprising:

a first contact hole filling in the first layer;7

a second contact hole filling in the second layer;7 and

an intermediate structure in the intermediate layer disposed between the first layer and the second layer and connecting said first contact hole filling with said second contact hole filling, said intermediate structure forming an interconnect having a length between longitudinal ends thereof ~~and a given width, and a contact area at each of said longitudinal ends with a contact area width contact area width greater than said~~

 given width, said interconnect having a contact area at each
of said longitudinal ends with a contact area width
perpendicular to said length, and a connecting structure
connecting said contact areas, said connecting structure
having a connecting structure area with a connecting structure
area width perpendicular to said length, said contact area
width being greater than said connecting structure area
width..

Claim 12 (previously added). The contact structure according to claim 11, wherein said interconnect is configured to connect two nearest points of a periodic basic grid disposed on said interconnect, to one another.

Claim 13 (previously added). The contact structure according to claim 12, wherein said contact area of said intermediate structure is a square contact area at each end of the interconnect.

Claim 14 (previously added). The contact structure according to claim 13, wherein the contact areas and the interconnect define a bone-shape form of said intermediate structure.

Claim 15 (previously added). The contact structure according to claim 11, wherein said intermediate layer is a

metallization plane, and said intermediate structure is formed of a conductive material of the metallization plane.

Claim 16 (previously added). The contact structure according to claim 11, wherein said contact hole fillings contain tungsten.

Claim 17 (previously added). The contact structure according to claim 11, wherein the first and second layers are oxide layers.

Claim 18 (previously added). The contact structure according to claim 11, wherein said first contact hole filling and said second contact hole filling are the only contact hole fillings contacting said intermediate structure.

Claim 19 (new). The contact structure according to claim 1, wherein said first contact hole filling and said second contact hole filling are laterally offset relative to one another.

Claim 20 (new). The contact structure according to claim 11, wherein said first contact hole filling and said second contact hole filling are laterally offset relative to one another.
